

MOSFET – Single, N-Channel, Gate ESD Protection, Small Signal, SC-75

20 V, 238 mA

NTA4001N, NVA4001N

Features

- Low Gate Charge for Fast Switching
- Small 1.6 x 1.6 mm Footprint
- ESD Protected Gate
- AEC-Q101 Qualified and PPAP Capable NVA4001N
- These Devices are Pb-Free and are RoHS Compliant

Applications

- Power Management Load Switch
- Level Shift
- Portable Applications such as Cell Phones, Media Players, Digital Cameras, PDA's, Video Games, Hand Held Computers, etc.

MAXIMUM RATINGS (T_J = 25 °C unless otherwise stated)

Parameter		Symbol	Value	Unit
Drain-to-Source Voltage		V _{DSS}	20	V
Gate-to-Source Voltage	Gate-to-Source Voltage		±10	V
Continuous Drain Current (Note 1)	Steady State = 25 °C	I _D	238	mA
Power Dissipation (Note 1)	Steady State = 25 °C	P _D	300	mW
Pulsed Drain Current	Pulsed Drain Current $t_P \le 10 \mu s$		714	mA
Operating Junction and Storage Temperature		T _J , T _{STG}	–55 to 150	°C
Continuous Source Current (Body Diode)		I _{SD}	238	mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		TL	260	°C

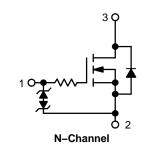
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	416	°C/W

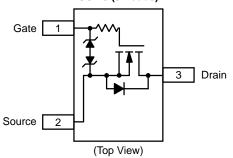
Surface-mounted on FR4 board using 1 in sq. pad size (Cu area = 1.127 in sq. [1 oz] including traces).

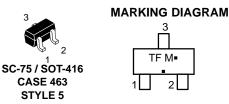
V _{(BR)DSS}	R _{DS(on)} Typ @ V _{GS}	I _D MAX (Note 1)
20 V	1.5 Ω @ 4.5 V	238 mA
20 0	2.2 Ω @ 2.5 V	200 1117 (



PIN CONNECTIONS

SC-75 (3-Leads)





TF = Specific Device Code

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

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ELECTRICAL CHARACTERISTICS (T_J = 25 °C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V}, I_D = 100 \mu\text{A}$	20			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 20 V			1.0	μΑ
Gate-to-Source Leakage Current	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 10 \text{ V}$			±100	μΑ
ON CHARACTERISTICS (Note 2)						
Gate Threshold Voltage	V _{GS(TH)}	$V_{DS} = 3 \text{ V}, I_{D} = 100 \mu\text{A}$	0.5	1.0	1.5	V
Drain-to-Source On Resistance	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 10 \text{ mA}$		1.5	3.0	
		$V_{GS} = 2.5 \text{ V}, I_D = 10 \text{ mA}$		2.2	3.5	Ω
Forward Transconductance	9FS	$V_{DS} = 3 \text{ V}, I_{D} = 10 \text{ mA}$		80		mS
CAPACITANCES						
Input Capacitance	C _{ISS}	$V_{DS} = 5 \text{ V, f} = 1 \text{ MHz,}$ $V_{GS} = 0 \text{ V}$		11.5	20	pF
Output Capacitance	Coss			10	15	
Reverse Transfer Capacitance	C _{RSS}	163 01		3.5	6.0	
SWITCHING CHARACTERISTICS (Note 3)						
Turn-On Delay Time	t _{d(ON)}	V_{GS} = 4.5 V, V_{DS} = 5 V, I_{D} = 10 mA, R_{G} = 10 Ω		13		ns
Rise Time	t _r			15		
Turn-Off Delay Time	t _{d(OFF)}			98		ns
Fall Time	t _f			60		1
DRAIN-SOURCE DIODE CHARACTERISTICS	•		-	-	-	-
Forward Diode Voltage	V _{SD}	$V_{GS} = 0 \text{ V}, I_{S} = 10 \text{ mA}$		0.66	8.0	V
Folward blode voltage	v _{SD}	v _{GS} = u v, ı _S = 10 mA		0.00	0.6	

Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
 Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES

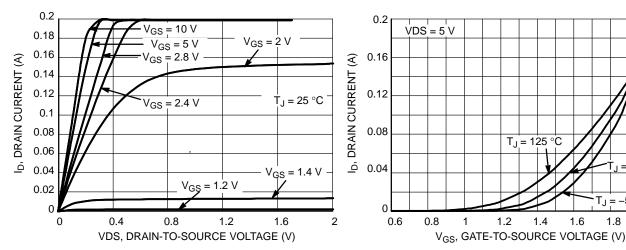


Figure 1. On-region Characteristics

Figure 2. Transfer Characteristics

= 25 °C

T_J = −55 °C

1.6

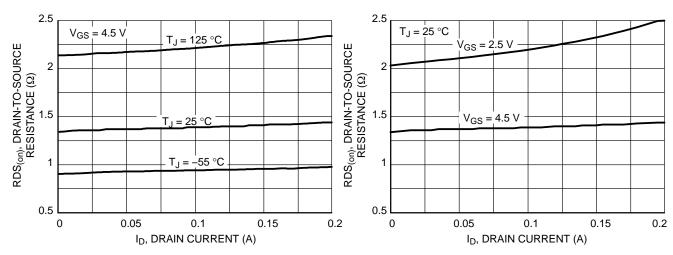


Figure 3. On-resistance versus Drain Current and Temperature

Figure 4. On-resistance versus Drain Current and Gate Voltage

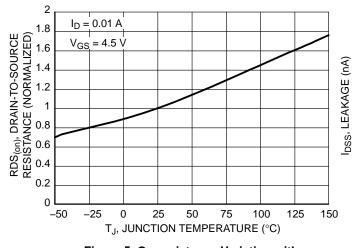


Figure 5. On-resistance Variation with **Temperature**

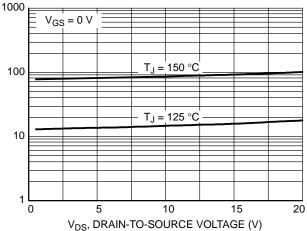
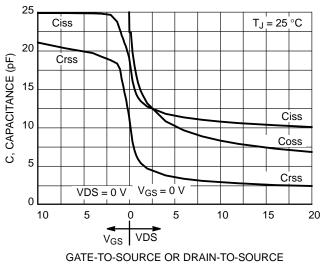


Figure 6. Drain-to-Source Leakage Current versus Voltage

TYPICAL PERFORMANCE CURVES



1000 $V_{DD} = 5 V$ $I_D = 10 \text{ mA}$ V_{GS} = 4.5 V 100 t_{d(off)} t, TIME (ns) t_{r} 10 t_{d(on)} 1 10 100 R_G , GATE RESISTANCE (Ω)

VOLTAGE (V)

Figure 7. Capacitance Variation

Figure 8. Resistive Switching Time Variation versus Gate Resistance

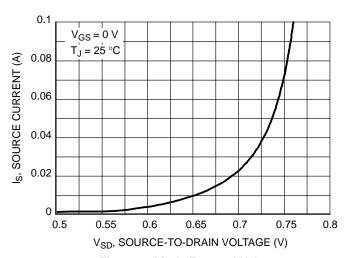


Figure 9. Diode Forward Voltage versus Current

ORDERING INFORMATION

Order Number	Package	Shipping [†]
NTA4001NT1G	SC-75 (Pb-Free)	3000 / Tape & Reel
NVA4001NT1G	SC-75 (Pb-Free)	3000 / Tape & Reel

[†] For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

REVISION HISTORY

Revision	Description of Changes	Date
3	Rebranded the Data Sheet to onsemi format.	6/26/2025

This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.



SC75-3 1.60x0.80x0.80, 1.00P

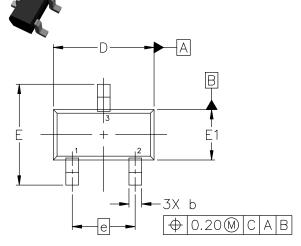
CASE 463 ISSUE H

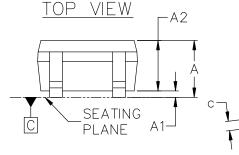
DATE 01 FEB 2024

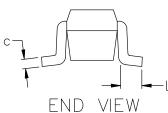


- 1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
- 2. ALL DIMENSION ARE IN MILLIMETERS.

DIM	MILLIMETERS			
DIM	MIN.	NOM.	MAX.	
А	0.70	0.80	0.90	
A1	0.00	0.05	0.10	
A2	0.80 REF.			
b	0.15	0.20	0.30	
С	0.10	0.15	0.25	
D	1.55	1.60	1.65	
Е	1.50	1.60	1.70	
E1	0.70	0.80	0.90	
е	1.00 BSC			
L	0.10	0.15	0.20	







SIDE VIEW

GENERIC MARKING DIAGRAM*



XX = Specific Device Code

M = Date Code

= Pb-Free Package

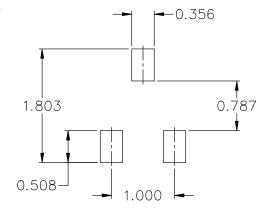
*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:	
PIN 1. BASE	
O ENTITED	

1. BASE 2. EMITTER 3. COLLECTOR STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES

REFERENCE MANUAL, SOLDERRM/D.

RECOMMENDED MOUNTING FOOTPRINT*



 STYLE 4:
 STYLE 5:

 PIN 1. CATHODE
 PIN 1. GATE

 2. CATHODE
 2. SOURCE

 3. ANODE
 3. DRAIN

DOCUMENT NUMBER:

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DESCRIPTION: SC75-3 1.60x0.80x0.80, 1.00P

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